

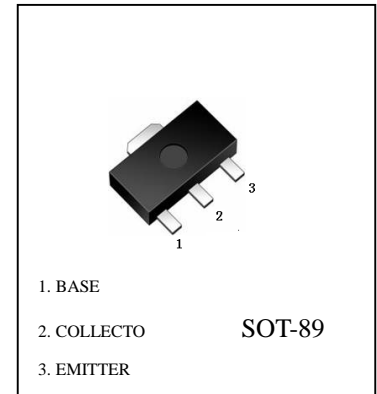
FEATURES

- High breakdown voltage.
- Adoption of MBIT process.
- Excellent hFE linearity.

Marking: CN

Maximum Ratings (Ta=25 °C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	400	V
Collector-Emitter Voltage	V _{CEO}	400	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current -Continuous	I _C	0.2	A
Collector Power dissipation	P _C	1.3	W
Storage Temperature	T _{stg}	-55to +150	°C

2SC4548 (NPN)


ELECTRICAL CHARACTERISTICS (@ Ta=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C =10uA, I _E =0	400			V
Collector- emitter breakdown voltage	V _{CEO}	I _C =10mA, I _B =0	400			V
Emitter- base breakdown voltage	V _{EBO}	I _E =10uA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =300V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =10V, I _C =50mA	60		200	
Base-emitter saturation voltage	V _{BE(sat)}	I _C =50mA, I _B =5mA			1	V
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =50mA, I _B =5mA		0.8		V
Transition frequency	f _T	V _{CE} =30V, I _C =10mA		70		MHz
Output capacitance	C _{ob}	V _{CB} =30V, I _E =0, f=1MHz		4		pF
Reverse Transfer Capacitance	C _{re}	V _{CB} =30V, I _E =0, f=1MHz		3		pF
Turn-ON Time	t _{on}	V _{CC} =150V, I _C =50mA, I _{B1} =I _{B2} =5mA		0.25		uS
Turn-OFF Time	t _{off}			5		uS

2SC4548 Typical Characteristics

